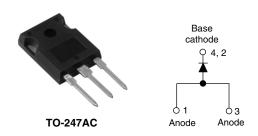




Vishay High Power Products

#### Input Rectifier Diode, 80 A



PRODUCT SUMMARY			
V <sub>F</sub> at 80 A	1.17 V		
I <sub>FSM</sub>	1450 A		
V <sub>RRM</sub>	800/1200 V		

#### **DESCRIPTION/FEATURES**

The 80EPS..PbF rectifier High Voltage Series has been optimized for very low forward voltage drop, with moderate leakage. The glass passivation technology used has reliable operation up to 150 °C junction temperature.



Typical applications are in input rectification and these products are designed to be used with Vishay HPP switches and output rectifiers which are available in identical package outlines.

This product has been designed and qualified for industrial level.

Compliant to RoHS directive 2002/95/EC.

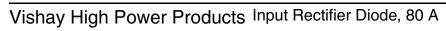
MAJOR RATINGS AND CHARACTERISTICS					
SYMBOL	CHARACTERISTICS	VALUES	UNITS		
I <sub>F(AV)</sub>	Sinusoidal waveform	80	A		
V <sub>RRM</sub>	Range	800/1200	V		
I <sub>FSM</sub>		1450	A		
V <sub>F</sub>	80 A, T <sub>J</sub> = 25 °C	1.17	V		
T <sub>J</sub>		- 40 to 150	°C		

VOLTAGE RATINGS					
PART NUMBER	V <sub>RRM</sub> , MAXIMUM PEAK REVERSE VOLTAGE V	V <sub>RSM</sub> , MAXIMUM NON-REPETITIVE PEAK REVERSE VOLTAGE V	I <sub>RRM</sub> AT 150 °C mA		
80EPS08PbF	800	900	1		
80EPS12PbF	1200	1300	I		

ABSOLUTE MAXIMUM RATINGS					
PARAMETER	SYMBOL	TEST CONDITIONS	VALUES	UNITS	
Maximum average forward current	I <sub>F(AV)</sub>	$T_C = 100$ °C, $180$ ° conduction half sine wave	80		
Maximum peak one cycle non-repetitive surge current	_	10 ms sine pulse, rated V <sub>RRM</sub> applied	1450	А	
	IFSM	10 ms sine pulse, no voltage reapplied	1500		
Maximum I <sup>2</sup> t for fusing	124	10 ms sine pulse, rated V <sub>RRM</sub> applied	10 500	A <sup>2</sup> s	
	l <sup>2</sup> t	10 ms sine pulse, no voltage reapplied	14 000		
Maximum I <sup>2</sup> √t for fusing	I <sup>2</sup> √t	t = 0.1 ms to 10 ms, no voltage reapplied 105 000		A²√s	

<sup>\*</sup> Pb containing terminations are not RoHS compliant, exemptions may apply

## 80EPS..PbF High Voltage Series





ELECTRICAL SPECIFICATIONS					
PARAMETER	SYMBOL	TEST CONDITIONS		VALUES	UNITS
Maximum forward voltage drop	$V_{FM}$	80 A, T <sub>J</sub> = 25 °C		1.17	V
Forward slope resistance	r <sub>t</sub>	T <sub>J</sub> = 150 °C		3.17	mΩ
Threshold voltage	V <sub>F(TO)</sub>			0.73	V
Maximum reverse leakage current	I <sub>RM</sub>	T <sub>J</sub> = 25 °C	V <sub>B</sub> = Rated V <sub>BBM</sub>	0.1	mA
		T <sub>J</sub> = 150 °C	VK = naieu VRRM	1.0	IIIA

THERMAL - MECHANICAL SPECIFICATIONS						
PARAMETER		SYMBOL TEST CONDITIONS		VALUES	UNITS	
Maximum junction and storage temperature range	е	T <sub>J</sub> , T <sub>Stg</sub>		- 40 to 150	°C	
Maximum thermal resistance, junction to case		R <sub>thJC</sub>	DC operation	0.35		
Maximum thermal resistance, junction to ambient		R <sub>thJA</sub>		40	°C/W	
Typical thermal resistance, case to heatsink		R <sub>thCS</sub>	Mounting surface, flat, smooth and greased	0.2		
Approximate weight			6	g		
			0.21	OZ.		
Mounting torque ———	minimum			6 (5)	kgf · cm	
	maximum			12 (10)	(lbf · in)	
Marking device			O	80EPS08		
			Case style TO-247AC (JEDEC)	80EPS12		



# Input Rectifier Diode, 80 A Vishay High Power Products

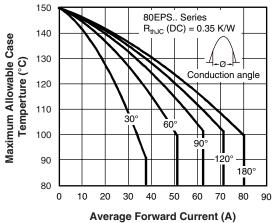


Fig. 1 - Current Rating Characteristics

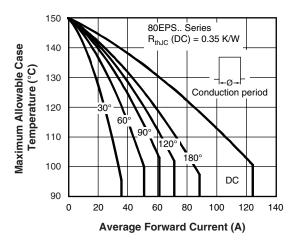


Fig. 2 - Current Rating Characteristics

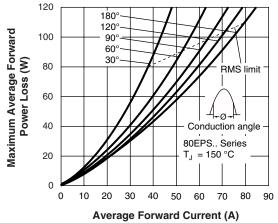


Fig. 3 - Forward Power Loss Characteristics

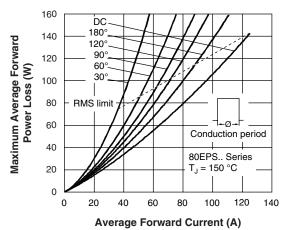
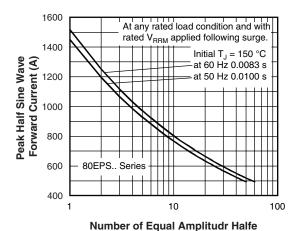


Fig. 4 - Forward Power Loss Characteristics



Cycle Current Pulse (N)
Fig. 5 - Maximum Non-Repetitive Surge Current

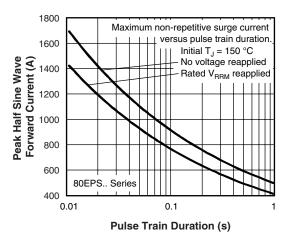


Fig. 6 - Maximum Non-Repetitive Surge Current

### 80EPS..PbF High Voltage Series

## Vishay High Power Products Input Rectifier Diode, 80 A



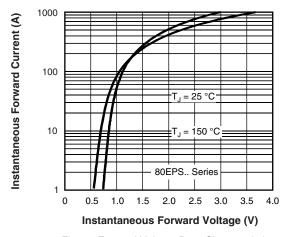


Fig. 7 - Forward Voltage Drop Characteristics

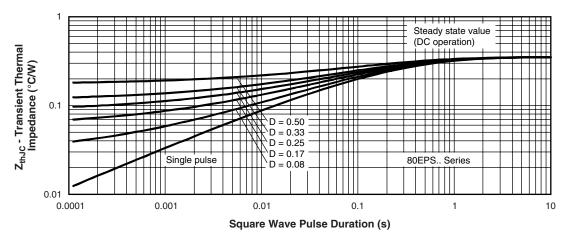


Fig. 8 - Thermal Impedance  $Z_{thJC}$  Characteristics

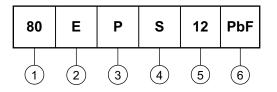


#### 80EPS..PbF High Voltage Series

Input Rectifier Diode, 80 A Vishay High Power Products

#### **ORDERING INFORMATION TABLE**

Device code



1 - Current rating (80 = 80 A)

2 - Circuit configuration:

E = Single diode

3 - Package:

P = TO-247AC

4 - Type of silicon:

S = Standard recovery rectifier

08 = 800 V 12 = 1200 V

5 - Voltage ratings

6 - None = Standard production

• PbF = Lead (Pb)-free

LINKS TO RELATED DOCUMENTS			
Dimensions <u>www.vishay.com/doc?95223</u>			
Part marking information	www.vishay.com/doc?95226		



Vishay

#### **Disclaimer**

All product specifications and data are subject to change without notice.

Vishay Intertechnology, Inc., its affiliates, agents, and employees, and all persons acting on its or their behalf (collectively, "Vishay"), disclaim any and all liability for any errors, inaccuracies or incompleteness contained herein or in any other disclosure relating to any product.

Vishay disclaims any and all liability arising out of the use or application of any product described herein or of any information provided herein to the maximum extent permitted by law. The product specifications do not expand or otherwise modify Vishay's terms and conditions of purchase, including but not limited to the warranty expressed therein, which apply to these products.

No license, express or implied, by estoppel or otherwise, to any intellectual property rights is granted by this document or by any conduct of Vishay.

The products shown herein are not designed for use in medical, life-saving, or life-sustaining applications unless otherwise expressly indicated. Customers using or selling Vishay products not expressly indicated for use in such applications do so entirely at their own risk and agree to fully indemnify Vishay for any damages arising or resulting from such use or sale. Please contact authorized Vishay personnel to obtain written terms and conditions regarding products designed for such applications.

Product names and markings noted herein may be trademarks of their respective owners.

Revision: 18-Jul-08

Document Number: 91000 www.vishay.com